Magnetoplasmons on graphene edge in quantizing magnetic field are investigated at different Landau level fillings. To find the mode frequency, the optical conductivity tensor of disordered graphene in magnetic field is calculated in the self-consistent Born approximation, and the nonlocal electromagnetic problem is solved using the Wiener-Hopf method. Magnetoplasmon dispersion relations, velocities and attenuation lengths are studied numerically and analytically with taking into account the screening by metallic gate and the energy dissipation in graphene. The magnetoplasmon velocity decreases in the presence of nearby gate and oscillates as a function of the filling factor because of the dissipation induced frequency suppression occurring when the Fermi level is located near the centers of Landau levels, in agreement with the recent experiments.

I. INTRODUCTION

Two-dimensional plasmons on graphene offer ample opportunities of applications due to wide tunability of their properties achieved by changing the doping level, confining charge carriers, by nanostructuring graphene or combining it with metal electrodes [1,2]. In magnetic field the plasmon resonance splits into two magnetoplasmon modes, as found using the terahertz spectroscopy of graphene disks [3,4]. The higher-frequency mode can be treated in the quasiclassical limit as two-dimensional plasma oscillations acquiring a frequency enhancement due to confining action of magnetic field [5,6]. The lower-frequency mode is localized near graphene edge and propagates only in one direction determined by a magnetic field orientation, so it can be guided along the edges and used to design plasmon circuits. Edge magnetoplasmons and possibilities of their manipulation were extensively studied in semiconductor-based quantum Hall systems (see, e.g., [7–10] and references therein).

In several recent experiments [11–15] the time-domain measurements of edge magnetoplasmon propagation on graphene were carried out, which allowed to directly determine their velocities. Similarly to that in semiconductor quantum wells [3,11], the velocity shows pronounced oscillations as a function of the Landau level filling factor, decreasing at non-integer fillings where the system is conducting and the dissipation is present. The presence of nearby metallic gate was also showed to reduce the plasmon velocity. Although the general theory of magnetoplasmons [16,17] allows to estimate their velocities, the effects of screening and dissipation are insufficiently studied from the theoretical point of view. The existing approaches for graphene magnetoplasmons [11,14,18] rely either on analytical formulas applicable for a clean system, or use the Drude approximation for graphene conductivity, that cannot describe the oscillating filling-factor dependencies originating from discreteness of Landau levels.

In this paper we provide the theoretical treatment of edge magnetoplasmons in graphene with taking into account gate screening, dissipation and the filling-factor dependence of graphene optical conductivity in quantizing magnetic field. In Sec. II we consider the electromagnetic part of the problem solved using the Wiener-Hopf method and estimate magnetoplasmon frequencies both in the absence and in the presence of dissipation. In contrast to conventional calculations of a complex frequency accounting for the damping, we consider a real frequency and a complex wave vector. In Sec. III we calculate the conductivity tensor of disordered graphene in quantizing magnetic field using the self-consistent Born approximation and length gauge which allow us to remove the $1/\omega$ divergence of conductivity and provide the qualitatively correct description of both its low-frequency and filling-factor dependencies, both being crucial to the theory of edge magnetoplasmons. In Sec. IV we show the results of numerical calculations of the magnetoplasmon dispersions and analyze how the velocity depends on the Landau level filling factor and on the distance between graphene and metal gate. In agreement with the experiments [11–15], we find the oscillating behavior of the velocity, which is suppressed by dissipation at non-integer Landau level fillings, and general reduction of the velocity by the gate screening. Our conclusions are presented in Sec. V.

II. ELECTROMAGNETIC PROBLEM

Consider the magnetoplasmon wave propagating along the graphene edge, which is directed parallel to the $y$ axis, with the frequency $\omega$ and wave vector $q$ (Fig. II). To take into account the damping, we assume the complex wave vector $q = q + i\alpha$ instead of a complex frequency. It is done in order to avoid complications arising in many-body calculations of the retarded conduc-
FIG. 1: Trajectories of negatively charged electrons deflected by magnetic field $\mathbf{B}$ and bouncing off the graphene edge, which participate in the formation of the magnetoplasmon mode propagating along the $y$ axis. The nearby metallic gate at the distance $d$ is shown at the bottom.

tivities at complex frequencies and conforms the setups of time-domain experiments where magnetoplasmon are attenuated in space. The graphene layer occupies the half-plane $x > 0$, $z = 0$. We take its conductivity tensor $\sigma_{x,\beta} = \sigma_{x,\beta}(\omega)\Theta(x)$ ($\Theta$ is the unit step function) in the long-wavelength limit $q \to 0$ and assume it to be spatially uniform at $x > 0$ and isotropic, $\sigma_{xx} = \sigma_{yy}$, $\sigma_{xy} = -\sigma_{yx}$.

Writing the continuity equation $\partial\rho/\partial t + \nabla \cdot j = 0$ for the charge density $\rho = \delta(z) e^{i(q_y \omega - q_x)} \rho(x)$ and the currents $j_x = -\sigma_{x,\beta} \nabla \varphi$ expressed in terms of the scalar potential $\varphi = e^{i(q_y \omega - q_x)} \varphi(x, z)$, we obtain [15, 18]

$$-i\omega \rho(x) = \Theta(x) \sigma_{xx}(\omega) (\partial_x^2 - \tilde{q}^2) \varphi(x, 0) + \delta(x) \sigma_{xx}(\omega) \partial_x \tilde{q} \sigma_{xy}(\omega) \varphi(x, 0). \quad (1)$$

The second equation arises from the three-dimensional Poisson equation $\varepsilon \nabla^2 \varphi = -4\pi \rho$, where $\varepsilon$ is the dielectric constant of the surrounding medium (we neglect the retardation in the low-frequency limit). Doing a Fourier transform along the $x$ axis and taking into account that $\varphi|_{z=-d} = 0$ due to the grounded metallic gate, we can recast it into the integral equation [16, 17]

$$\varphi(x, 0) = \frac{4\pi}{\varepsilon} \int_0^{\infty} dx' L_{\tilde{q},d}(x - x') \rho(x'). \quad (2)$$

with the kernel

$$L_{\tilde{q},d}(x) = \int_{-\infty}^{+\infty} \frac{dk}{2\pi} \frac{e^{ikx}}{\sqrt{k^2 + \tilde{q}^2}} \left[ 1 + \coth(d\sqrt{k^2 + \tilde{q}^2}) \right]. \quad (3)$$

The system of equations (1)-(3) determines the electromagnetic modes in the system. We can solve it using the Wiener-Hopf method following Ref. [17] with the only difference that we assume a real frequency $\omega$ and a complex wave vector $\tilde{q}$ instead of complex $\omega$ and real $q$. The final equation for edge magnetoplasmon dispersion is

$$1 + \frac{\sigma_{xy}(\omega)}{i \sigma_{xx}(\omega)} \tanh Z(\tilde{q}, \omega) = 0, \quad (4)$$

where

$$Z(\tilde{q}, \omega) = \frac{1}{2\pi} \int_{-\infty}^{+\infty} \frac{\tilde{q} \, dk}{k^2 + \tilde{q}^2} \times \ln \left\{ 1 + \frac{4\pi i \sigma_{xx}(\omega)}{\varepsilon \omega} \frac{\sqrt{k^2 + \tilde{q}^2}}{1 + \coth(d\sqrt{k^2 + \tilde{q}^2})} \right\}. \quad (5)$$

Here $\tilde{q}$ is assumed to have a positive real part, otherwise we need to replace it by $-\tilde{q}$.

Introducing the dimensionless quantity $\eta = 4\pi \tilde{q} \sigma_{xx}(\omega)/i\varepsilon$ [18], we can find $Z$ as a function of $\eta$ and $\tilde{q} d$. We are interested in the long-wavelength and low-frequency limit, when $\tilde{q}, \omega \to 0$ and $\eta \propto \sigma_{xx}(0)$. In the case of low dissipation we can assume $|\eta| \ll 1$, $\tilde{q} \approx q$, and calculate the analytical asymptotics [17] of $Z$ in this limit:

$$Z \approx -\frac{\eta}{2\pi} \log \left( -\frac{4\varepsilon d}{\varepsilon q} \right), \quad q d \gtrsim e^{-\gamma_E}, \quad (6)$$

$$Z \approx -\frac{\eta}{2\pi} \log \left( -\frac{4\varepsilon^{1+\delta} q d}{\eta} \right), \quad |\eta| \lesssim q d \lesssim e^{-\gamma_E}, \quad (7)$$

$$Z \approx \sqrt{-\eta q d}, \quad q d \lesssim \frac{|\eta|}{4\varepsilon^{1+\delta} q d}. \quad (8)$$

where $\gamma_E \approx 0.577$ is the Euler gamma constant. Eq. (6) corresponds to the case where the gate is either absent or too far to influence the magnetoplasmons. Eq. (7) corresponds to the opposite limit of local capacitance approximation [19], where (2) reduces at small $d$ to the local relationship for the plane capacitor: $\varphi(x) = 4\pi \varepsilon d \rho(x)/\varepsilon$. Substituting (6) and (8) into (4), we obtain the dispersion relations for the edge magnetoplasmons [17]:

$$\omega = \frac{-2q \sigma_{xy}(0)}{\varepsilon} \ln \frac{2\varepsilon}{qw}, \quad q d \gtrsim e^{-\gamma_E}, \quad (9)$$

$$\omega = \frac{-2q \sigma_{xy}(0)}{\varepsilon} \ln \frac{2\varepsilon^{1+\delta} q w}{2\varepsilon^{2\delta} q w}, \quad q w \lesssim q d \lesssim e^{-\gamma_E}, \quad (10)$$

$$\omega = \frac{-2\pi \varepsilon \sigma_{xy}(0)}{\varepsilon} \sqrt{\frac{2q d}{w}}, \quad q d \lesssim \frac{qw}{2\varepsilon^{1+\delta} q w}. \quad (11)$$

where $w = -(2\pi/\varepsilon)[d \ln \sigma_{xx}(\omega)/d\varepsilon]|_{\omega=0}$. Since $\sigma_{xy}(0) < 0$ at $\mathbf{B} \propto \mathbf{e}_z$, we have the edge mode propagating in the positive $y$ direction (Fig. [1]).

In the presence of dissipation the expressions (9)-(11) are inaccurate because in the long-wavelength and low-frequency limit probed in the experiments [15, 16] the damping rate dominates the frequency therefore the real part of $\sigma_{xx}$ dominates the imaginary part connected with $w$ (in other words, the dissipation dominates electron inertial motion). Using (6) and (8) in (4) at $\omega \to 0$, we obtain the approximations for dispersion law and attenuation rate $\alpha$. At large graphene-to-gate distance $q d \gtrsim 1$ we obtain

$$\omega = \frac{\pi q \sigma_{xx}(0)}{\varepsilon \varepsilon \ln Y}, \quad \alpha = -\frac{\alpha}{\ln Y}, \quad (12)$$
where $Y$ is the complex solution of the equation $1 - iXY \ln Y = 0$ with $Re Y < 0$, $Im Y > 0$, and $X = -2e\sigma_{xy}(0)/\pi \sigma_{xx}(0)$. At very small distances, when $qd \lesssim 0.01$, we obtain

$$\omega = \frac{8\pi q^2 \sigma_{yy}(0)}{\varepsilon \sigma_{xx}(0)}, \quad \alpha = q. \quad (13)$$

Note that, in contrast to the long-wavelength limit of the solution in Ref. [19] with complex $\omega$ and real $q$, where $\omega$ is purely imaginary, here we have the oscillations highly damped in space with $\tilde{q} = q(1 + i)$. At larger distances or wave vectors, when $qd > 0.01$, the dispersion becomes linear and attenuation rate decreases.

### III. OPTICAL CONDUCTIVITY IN MAGNETIC FIELD

To calculate the optical conductivity tensor $\sigma_{\alpha \beta}$ in disordered graphene in quantizing magnetic field we use the version of the self-consistent Born approximation [20] which allows us to take into account both formation of Landau levels and their disorder-induced broadening. In this approximation the single-electron Green functions are dressed by interaction with random disorder potential, which results in broadening of each Landau level, and then the current vertex is modified by a disorder ladder. Direct application of the Kubo formula to calculate the current response to the oscillating vector potential $A = (e/\omega)E \propto e^{-i\omega t}$ provides the dynamical conductivity

$$\delta \sigma_{\alpha \beta}(q, \omega) = \frac{i\hbar}{e\omega} \mathcal{G}^{R}_{j_{\alpha}j_{\beta}}(q, \omega) \quad (14)$$

in terms of the Fourier transform $\mathcal{G}^{R}_{j_{\alpha}j_{\beta}}(q, \omega) = -iS^{-1} \int d\mathbf{r} d\mathbf{r}' \int_{-\infty}^{\infty} dt \ e^{-i\mathbf{q(r-r')}} e^{i\omega t} \langle [j_{\alpha}(\mathbf{r}, t), j_{\beta}(\mathbf{r}', 0)] \rangle$ of the retarded Green function of the current $j_{\alpha}(\mathbf{r}, t) = e^{i\mathbf{p}\mathbf{r} + i\omega t} \sigma_{\alpha \beta} \psi(\mathbf{r}, t)$. Here $\psi(\mathbf{r}, t)$ is the two-component Heisenberg field operator of massless Dirac electrons in the valley $K$ of graphene, $e^{i\mathbf{p}\mathbf{r}} \approx 10^6 \text{m/s}$ is the Fermi velocity, $g = 4$ is the degeneracy over the valleys and spin projections, $S$ is the system area.

However, as noted in Ref. [23], due to the prefactor $1/\omega$ in (14), this form of conductivity does not obey the Kramers-Kronig relations and diverges in the limit $\omega \to 0$ which we are interested in. To obtain a correct low-frequency behavior we need either to calculate $\sigma_{xy}$ in the $\mathbf{p} \cdot \mathbf{A}$ gauge with paying attention to its causality properties of to use the $\mathbf{E} \cdot \mathbf{r}$ gauge. The latter can be applied in the dipole long-wavelength limit $qd < 1$ probed in the experiments [11,13], where $l_H = \sqrt{\hbar c/eB}$ is the magnetic length defining the spatial scale of Landau level wave functions. Using the commutation relations $[H, r_n] = -i\hbar v_F \sigma_n$ and the spectral representation

$$\mathcal{G}^{R}_{j_{\alpha}j_{\beta}}(q, \omega) = \int_{-\infty}^{\infty} d\omega' \frac{S_{j_{\alpha}j_{\beta}}(\omega')}{\omega - \omega' + i\delta}, \quad (15)$$

we find that both methods give the same result for the optical conductivity

$$\sigma_{\alpha \beta}(\omega) = \frac{i\hbar}{\omega} \int_{-\infty}^{\infty} d\omega' \frac{S_{j_{\alpha}j_{\beta}}(\omega')}{\omega - \omega' + i\delta} \quad (16)$$

at $q \to 0$ in terms of the spectral function $S_{j_{\alpha}j_{\beta}}$; here $\delta \to +0$.

The self-consistent Born approximation provides the following expression for the Green function of currents (see also [20, 21]):

$$\mathcal{G}^{R}_{j_{\alpha}j_{\beta}}(0, \omega) = -\frac{e^2 \tilde{q}^2}{2\pi \hbar^2 l_H} \sum_{n_1n_2} \int_{-\infty}^{\infty} F^{n_1n_2}_{\alpha \beta} \frac{dz}{1 - \gamma_{n_1n_2} G_{n_1} G_{n_2}^{*}} \times \left\{ \frac{\nu_F(z) G_{n_1} \ln G_{n_2}}{1 - \gamma_{n_1n_2} G_{n_1} G_{n_2}^{*}} + \frac{\nu_F(z + \omega) \ln G_{n_1} G_{n_2}^{*}}{1 - \gamma_{n_1n_2} G_{n_1} G_{n_2}^{*}} \right\}, \quad (17)$$

where $G_{n_1} \equiv G_{n_1}^{R}(z + \omega)$ and $G_{n_2} \equiv G_{n_2}^{R}(z)$ are the retarded Green functions of electrons on Landau levels with the numbers $n_1, n_2 = 0, \pm 1, \pm 2, \ldots$, $\nu_F(z) = \left\{ \left[ (\hbar z - \gamma_{n_1n_2})/\sqrt{2} \right] + 1 \right\}$ is the Fermi-Dirac distribution, $\gamma_{n_1n_2} = (2\pi \hbar^2 n_1 n_2)/(\hbar^2 S^{2}) \sum_{k} \langle \left\langle (\psi_{n_1k}^R | U | \psi_{n_2k}) (\psi_{n_2k}^R | U | \psi_{n_1k}) \right\rangle \rangle_U$ is the matrix element of the disorder potential $U$ averaged over its realizations, which appears in the disorder ladder, $\psi_{nk}$ is the electron state on the nth Landau level with the kth guiding center index. The factor $F^{n_1n_2}_{\alpha \beta} = 2^{n_1 + n_2 - 2} (f_{\alpha} f_{\beta} f_{n_1 - 1} | f_{n_2} f_{n_1} | f_{n_1 - 1} f_{n_2})$ with $f_{n} = 1$, $f_{0} = i$ determines the selection rules $|n_1| = |n_2| \pm 1$ for the dipole inter-Landau level transitions in graphene.

Eq. (17) takes the simple form in the case of short-range impurities, when $\gamma_{n_1n_2} \to \infty$ [21, 22]. In this case we can take the electron Green functions $G_{n}^{R}(\omega) = \int d\omega' \rho_n(\omega')/(\omega - \omega' + i\delta)$ corresponding to the Lorentzian spectral density $\rho_n(\omega) = (\hbar \Gamma/\pi)/(\hbar \omega - E_n)^2 + \Gamma^2$, instead of half-elliptic densities [20, 22] appearing as an artefact of the self-consistent Born approximation. Here $E_n = \nu_F(n) h \nu_F \sqrt{2}|n|/l_H$ and $\Gamma$ are, respectively, the energy and the width of the nth Landau level. We assume equal widths of all Landau levels, in agreement with the scanning tunneling spectroscopy experiments (see, e.g., [21]). From (15)–(17) we obtain the final expression for the conductivity, which obeys the Kramers-Kronig relations and behaves correctly in the $\omega \to 0$ limit:

$$\sigma_{\alpha \beta} = \left\{ \frac{i e^2 \nu_F^2}{2\pi \hbar^2 l_H} \sum_{n_1n_2} F^{n_1n_2}_{\alpha \beta} \int d\omega' d\omega \frac{\nu_F(z) \rho_n(z)}{(z - z')(\omega + \omega' + i\delta)} \times \frac{\nu_F(z') \rho_n(z')}{(z' - z)(\omega + \omega' + i\delta)} \right\} \quad (18)$$

The integrals in (15) can be calculated analytically in the limit $T \to 0$, $\nu_F(z) \to 0$($\mu - h\omega$), corresponding to the experiments [11, 13] carried out at cryogenic temperatures. The chemical potential $\mu$ can be connected with the Landau level filling factor: $\nu = g \sum_{n} \frac{1}{2} \text{sgn}(n) + \int dz \nu_F(z) \rho_n(z)$; $\nu$ is zero for undoped graphene, where
FIG. 2: Solid lines: real and imaginary parts of $\sigma_{xx}$ (a,b) and $\sigma_{xy}$ (c,d) as functions of $\omega$ calculated when the Fermi level is located in the center of the 1st Landau level, $\nu = 4$ (a,c), or between the 1st and 2nd levels, $\nu = 6$ (b,d). Calculations are conducted at $B = 12$ T, $\Gamma = 5$ meV. Dotted lines: Drude conductivities calculated at the same carrier density in the same magnetic field with $\gamma = 2\Gamma/h$. Insets in (b) and (c) show the filling-factor dependencies of, respectively, static resistivity $\rho_{xx}(0)$ and Hall conductivity $\sigma_{xy}(0)$ (solid lines) and their Drude counterparts (dotted lines).

the 0th Landau level is half-filled, and increases by 4 for each fully filled Landau level because of the fourfold degeneracy of electron states, so it equals $4n + 2$ when the $n$th level is completely filled and $4n$ when the $n$th level is half-filled. We do not take into account Zeeman splitting and formation of fractional Hall states because they become important either in very high magnetic fields of in very clean samples.

In the limit of high doping or low magnetic field, when the chemical potential $\mu$ is located between $E_n$ and $E_{n+1}$, a single intraband transition $n \rightarrow n + 1$ provides a major contribution to (18). In the limit $n \gg 1$ it takes the form of the classical Drude conductivity in magnetic field

$$\sigma_{xx}(\omega) = \frac{n_c e^2}{m^*} \frac{i(\omega + i\gamma)}{(\omega + i\gamma)^2 - \omega_c^2},$$

$$\sigma_{xy}(\omega) = \frac{n_c e^2}{m^*} \frac{\omega_c}{(\omega + i\gamma)^2 - \omega_c^2},$$

where $n_c = \nu/2\pi l^2_H$ is the two-dimensional carrier density, $m^* = m/\sqrt{\epsilon}$ and $\omega_c = eB/\sqrt{\epsilon}c$ are, respectively, the cyclotron mass and frequency, and $\gamma = 2\Gamma/h$ is the decay rate of an electron-hole pair.

Examples of $\sigma_{\alpha\beta}(\omega)$ calculated from (18) in the Drude model (19)–(20) at the same carrier density are shown in Fig. 2. When the Fermi level is located between Landau levels [Fig. 2(b,d)], the conductivity behavior at low frequencies is close to the Drude model predictions, especially at high filling factors. At non-integer filling of Landau levels [Fig. 2(a,c)], the conductivity deviates from the Drude model. Note the marked increase of $\sigma_{xx}$ at low frequencies $|\omega| \lesssim \Gamma$ indicating the dissipation due to intralevel transitions. The second important difference is the positive derivative $d\Im \sigma_{xx}(\omega)/d\omega|_{\omega=0} > 0$ at the half-integer filling in Fig. 2(a), which is indicative of effectively free electrons moving within the Landau level at $|\omega| \lesssim \Gamma$, being in contrast to the negative $d\Im \sigma_{xx}(\omega)/d\omega|_{\omega=0} < 0$ at the integer filling in Fig. 2(c) typical to bound electrons. In the latter case this derivative is related to the quantity $w$ in (19)–(14), which can be interpreted (17) as a distance where the energy of two-dimensional plasma oscillations is comparable with the cyclotron energy. At half-integer fillings, when the dissipation is significant, this quantity has no such meaning, and the formulas (9)–(11) are inapplicable as well.

Although our conductivity demonstrates the qualitatively correct low-frequency properties and properly takes into account the Landau level quantization, further improvement is needed to achieve quantitative agreement with the experiment. For example, the peaks in the static $\rho_{xx}(0)$ [see inset in Fig. 2(b)] and the simultaneously occurring rising parts in the dependence of $\sigma_{xy}(0)$ on $\nu$ between the quantized plateaus [inset in Fig. 2(c)] characteristic to conducting states at non-integer Landau level fillings are broader than in the typical quantum Hall effect measurements (11, 22). From the other side, the broadening of these peaks at nonzero frequencies studied in semiconductor quantum wells (26, 27) should also been taken into account. The conductivity model which explicitly includes consideration of localized and extended states would provide more accurate results in the low-frequency region.

IV. CALCULATION RESULTS

Using the formulas (9), (10), (13), we can calculate numerically the dispersion relations $\omega(q)$ and attenuation rates $\alpha(q)$ at different filling factors $\nu$ and graphene-to-gate distances $d$ to study the effects of gate screening and dissipation. We take the parameters $B = 12$ T, $\Gamma = 5$ meV, $\varepsilon = 4$, which are close to the experimental conditions (11, 15) where Landau quantization is well developed.

In Fig. 3 we show typical examples of $\omega(q)$ and $\alpha(q)$ calculated in the absence of the gate screening, at $d = \infty$, with the full Landau-level based conductivities (18) and within the Drude model (19)–(20) at the same carrier density. At integer Landau level fillings $|\nu| = 6$, Fig. 3(b,d)] $\omega$ and $\alpha$ are, respectively, slightly higher and significantly lower than in the Drude model. This indicates that the dissipation, which suppresses $\omega$ and increases $\alpha$, is lower than in the Drude model due to the inter-Landau level gap. At half-integer Landau level fill-
ings \( \nu = 4 \), Fig. 3[a,c]) the situation is opposite: the dissipation caused by the intralevel transitions slightly suppresses \( \omega \) and significantly increases \( \alpha \) in comparison with the Drude model. Note also the pronounced dissipation-induced decrease of \( \omega \) and increase of \( \alpha \) at \( \nu = 4 \) in comparison with \( \nu = 6 \). The numerical calculations in both models are close to the analytical approximation \( \text{(12)} \) where the corresponding conductivities at \( \omega = 0 \) are substituted. For comparison we plotted the magneto-plasmon frequency calculated with the Drude conductivity of a clean \((\gamma = 0)\) system, which is higher than in the disordered system and agrees with the analytical approximation \( \text{(13)} \) very well.

The similar calculation results in the presence of the screening gate at \( d = 200 \text{ nm} \) are shown in Fig. 4. We see the overall suppression of \( \omega \) in comparison with the ungated case, which becomes even stronger in the presence of dissipation. At integer \( \nu = 6 \), Fig. 4[b,d] and half-integer \( \nu = 4 \), Fig. 4[a,c] Landau level fillings we again see the effect of, respectively, decreased and enhanced dissipation on \( \omega \) and \( \alpha \). The analytical approximation \( \text{(13)} \) predicting highly damped mode with quadratic dispersion at small \( d \) is applicable only at very low distances or wave vectors, \( qd \ll 0.01 \), while at higher \( q \) the dispersion laws become linear. Calculations with the Drude conductivity of a clean system agree with \( \text{(13)} \) and provide considerably higher \( \omega \).

In Fig. 5 we show the edge magneto-plasmon phase velocity \( v = \omega / q \) and quality factor \( Q = q / 2 \alpha \) calculated at \( q = 0.2 \mu \text{m}^{-1} \) (where dispersions are almost linear) as functions of the filling factor \( \nu \) both in the absence and in the presence of the metallic gate. As expected from the aforementioned dissipation-induced frequency suppression, we observe the dips in both \( v \) and \( Q \) when the Fermi level is located in the centers of Landau levels \((\nu = 4, 8, 12, 16)\). In Fig. 5[a] these dips are slightly displaced to the left, perhaps, due to the general rising trend of \( v(\nu) \), and also demonstrate some extra oscillations, which can be an artefact of the model used to calculate the conductivity. On the contrary, when the Fermi level is located in the middle of any inter-Landau level gap \((\nu = 2, 6, 10, 14)\), \( v \) and \( Q \) have peaks due to reduced dissipation. The oscillations of \( v(\nu) \) and \( Q(\nu) \) occur around the smooth results of the quasiclassical Drude model, which is insensitive to how the individual Landau levels are filled. Comparison with the calculations for a clean system shows that the gate screening not only reduces the velocity, but also enhances the dissipation-induced suppression of \( v \) and \( Q \). As in the previous picture, the analytical formula \( \text{(12)} \) well describes the dispersion and damping at \( d = \infty \), while the formula \( \text{(13)} \) for small \( d \) is applicable only in the regions of low velocity and high dissipation.

V. CONCLUSIONS

We considered the magneto-plasmon modes propagating along graphene edge in quantizing magnetic fields in the presence of the grounded metallic gate. The relationship between real frequencies and complex wave vectors (with the imaginary part responsible for the damp-
the points show analytical approximations. The notations for
discontinuities, and with Drude conductivity in a clean system, and
results with Landau-level based (LL) and Drude conductiv-
ty tensor method in a form of algebraic equation (4)–(5). The op-
erating) of these modes was obtained using the Wiener-Hopf
curves and points on the panels (a,c) and (b,d) are the same
ε
Γ = 5 meV,
life time of the edge magnetoplasmon are increased in
the dissipation is low, and the frequency, velocity and
make the following conclusions:
for comparison. The magnetoplasmon dispersions, at-
crved Landau level, the dissipation is enhanced due to
intralevel transitions, and the frequency, velocity and life
time of the edge magnetoplasmon are suppressed. So
our approach predicts the oscillations of the edge mag-
netoplasmon velocity when the filling factor is changed,
which are superimposed on the smooth trend of growing
velocity as the carrier density increases. The commonly
used [6] Drude conductivity model describes only the
latter because does not take into account Landau level
quantization.
(b) The electric field screening caused by a nearby
metallic gate decreases the frequency and velocity of the
mode, and makes its dissipation-induced suppression
at non-integer filling of Landau levels much more pro-
nounced.
(c) The analytical formulas [9]–[11] for the mode
frequency, which are frequently used to analyze the experi-
mental data [11–12], are applicable only for very clean
systems. The quantity \( v \) entering these formulas lose its
meaning at half-integer Landau level fillings, when the
dissipation is significant. Eq. (12) can be used instead
in the case when the gate screening is negligible. The
important feature of the experimental conditions is that
plasmons are probed at relatively low frequencies not ex-
ceeding the terahertz range, so any realistic rate of dis-
sipation due to inter-Landau level transitions dominates
the frequency and substantially modify mode properties
in comparison with the predictions for a clean system.
Our conclusions are in qualitative agreement with the
experimental data [11–12], where the suppression of the
magnetoplasmon velocities at non-integer Landau level
fillings was observed. Our approach assume the abrupt
dge of graphene and does not take into account the de-
tails of spatial structure of Landau level wave functions
near the edge, which include formation of incompressible
stripes [19], edge channels [9, 14, 28], and electron drift
due to electric field normal to the edge [12, 13]. Analysis
of these details requires an essential complication of our
approach and is beyond the scope of this paper.
To study the effects of Landau level filling on the edge
magnetoplasmon we used the model for the optical con-
ductivity providing qualitatively correct description of the
low-frequency behavior and the filling-factor de-
dence. A refined model, which takes into account the
localized states and their scaling properties, can provide
an additional insight into the theory of edge magnetopo-
lasons in quantum Hall regime and bring the results
of our approach into better quantitative agreement with
the experiments.

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FIG. 5: Edge magnetoplasmon velocities \( v \) (a,b) and quality
factors \( Q \) (c,d) as functions of the Landau level filling factor \( \nu \)
at \( q = 0.2 \mu m^{-1} \) in the absence \([d = \infty, (a,c)]\) and in the pres-
ence \([d = 200 \text{ nm}, (b,d)]\) of the gate screening at \( B = 12 \text{ T},
\Gamma = 5 \text{ meV}, \varepsilon = 4 \). The curves show numerical calculation
results with Landau-level based (LL) and Drude conductiv-
ities, and with Drude conductivity in a clean system, and
the points show analytical approximations. The notations for
curves and points on the panels (a,c) and (b,d) are the same
as in, respectively, Figs. 3 and 4.

The analysis of the calculation results allows us to
make the following conclusions:
(a) At integer filling of Landau levels \( (\nu = 2, 6, 10, \ldots) \),
where the Fermi level is located in the interlevel gap,
dissipation is low, and the frequency, velocity and
life time of the edge magnetoplasmon are increased in
comparison to the predictions of the Drude model. On
the contrary, at half-integer filling of Landau levels \( (\nu = 
4, 8, 12, \ldots) \), where the Fermi level lies within a broad-
ened Landau level, the dissipation is enhanced due to
intralevel transitions, and the frequency, velocity and life
time of the edge magnetoplasmon are suppressed. So
our approach predicts the oscillations of the edge mag-
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